



College of Optical Sciences  
THE UNIVERSITY OF ARIZONA



# **Unified first-principle analysis of ultraintense laser-matter interactions: Theory, computations and experiments**

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# **Program goals:**

- 1. Devise first-principle models of the interaction of fs laser pulses with materials (both on surfaces and inside transparent materials);  
implement models in numerical codes**
- 2. Develop non-perturbative ionization models and incorporate them in the codes**
- 3. Conduct experiments to support and verify modeling:**
  - Pump-probe imaging of ablation with ultrashort probe (5 fs)**
  - Pump-probe imaging of ablation of microdroplets with XUV probe**
- 4. Experimentally study exotic ablation situations:**
  - Confined microexplosions inside transparent solids and on interfaces**
  - Ablation with ultrashort laser pulses ~5 fs**
  - Ablation with fs pulses in the wavelength range 200 nm – 2.6  $\mu\text{m}$**
  - Effects of pulse shaping in ablation**

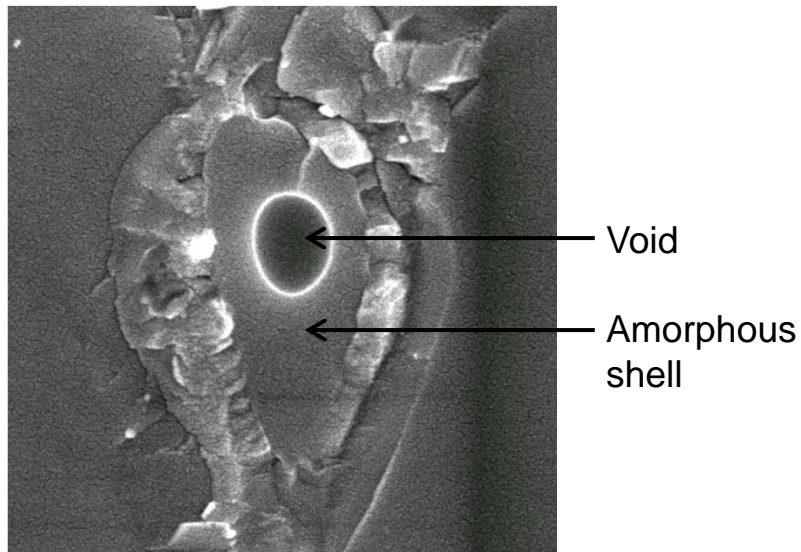


# First-principle models of fs laser-matter interactions

**Model #1** – modeling high-NA fs beam propagating inside a dielectric

**Non-paraxial Maxwell propagator coupled with rate equations for ionization and electron heating**

**Simulate first  $<100\text{fs}$   $\rightarrow$  lattice remains cold**



## **Practical goals:**

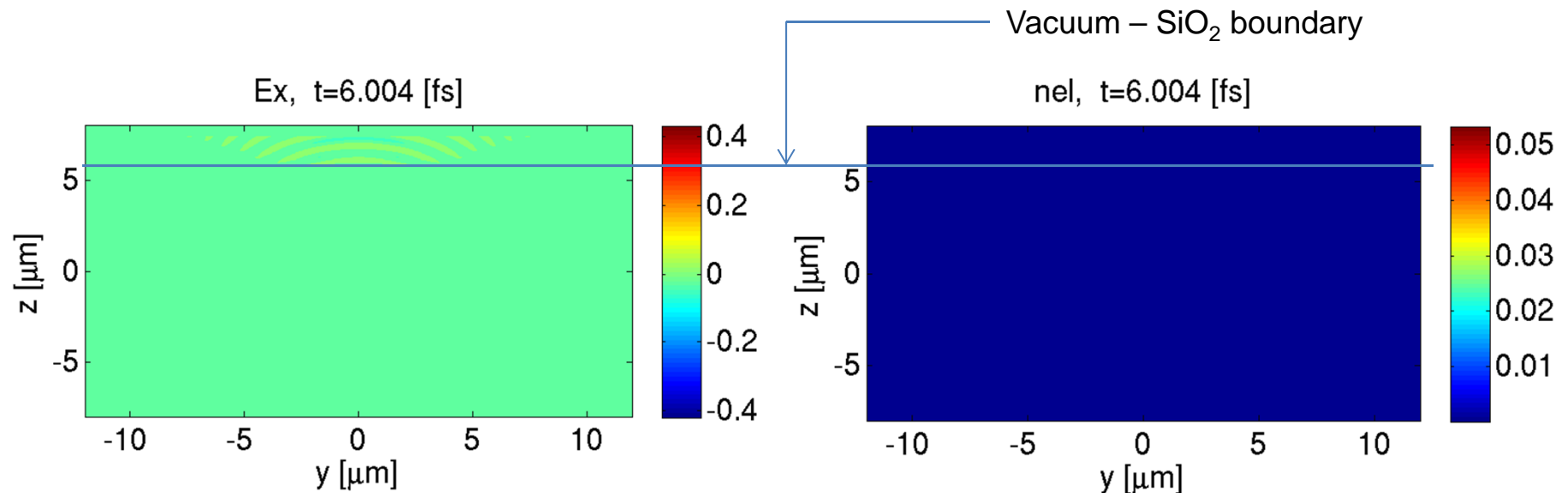
- Compute distribution of energy absorbed inside dielectric
- Maximize absorbed energy via tailoring beam and pulse shapes
  - $\rightarrow$  Create larger voids
  - $\rightarrow$  Create more extreme pressures and temperatures



# Computationally challenging – need to resolve significantly sub-wavelength spatial transients (moving skin layers ~ 10 nm – thick at max. ionization)

Preliminary results in full 3D – Brute force approach: Constant grid size < Skin depth

- Full 3D simulation
- 800nm wavelength, 100fs pulse
- Ionization limited at  $n_e = 3 \cdot 10^{27} \text{ cm}^{-3}$  (~1.5 times critical density, skin depth = 175 nm)
- 32 processors, uniform 20 nm grid, 5 hours computation time



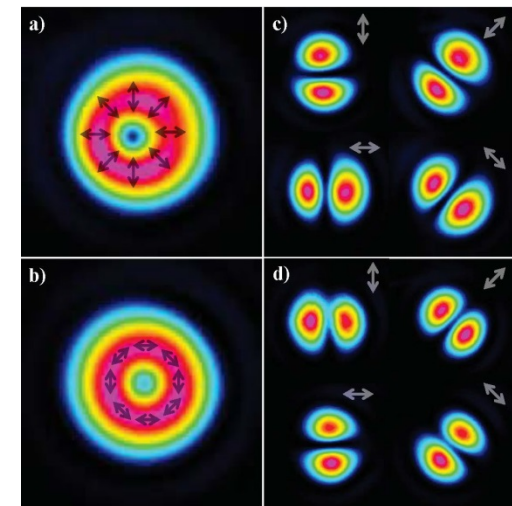


## Model #1 – future work

- Brute force in 3D with full ionization is impractical: ~50 years/computation
- Approaches:
  - Variable (but static) grid across computational domain
  - Adaptive grid
  - 2D (x,z,t) - corresponds to cylindrical focusing, axial microexplosion
  - 2D (r,z,t) – corresponds to 3D with azimuthal or radial polarization, realizable through polarization beam shaping with S-plate

- S-plate is a micro-structured optical polarization converter
- Converts linear into azimuthal or radial polarizations
- Produces large longitudinal field in focus

M. Beresna, M. Gecevicius, P. Kazansky, T. Gertus  
 “Radially polarized optical vortex converter created  
 by femtosecond laser nanostructuring of glass”,  
 APL **98**, 201101 (2011)



- Implement different (empirical and rigorous) ionization models in the code

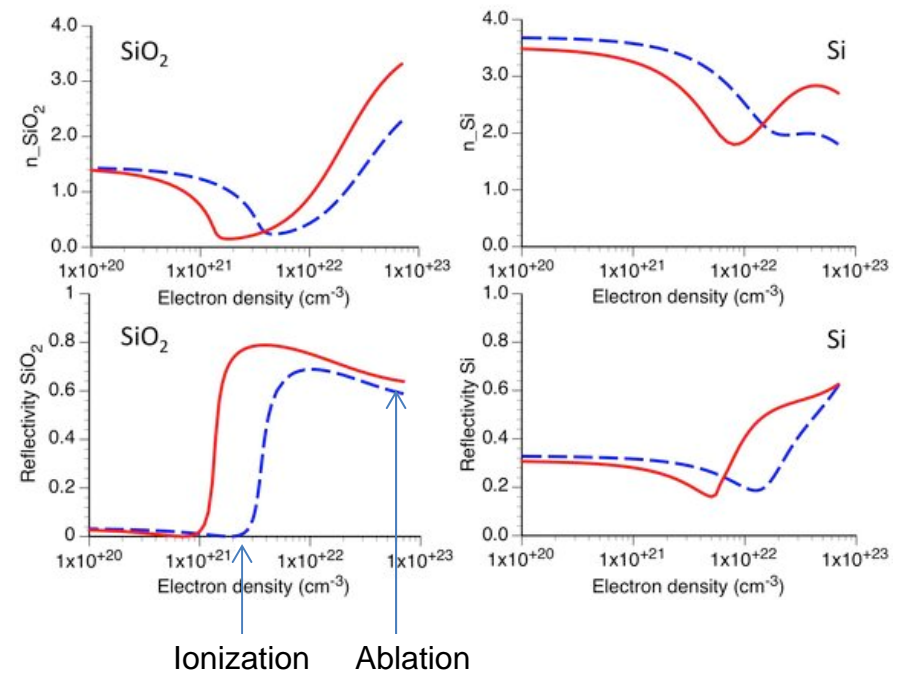
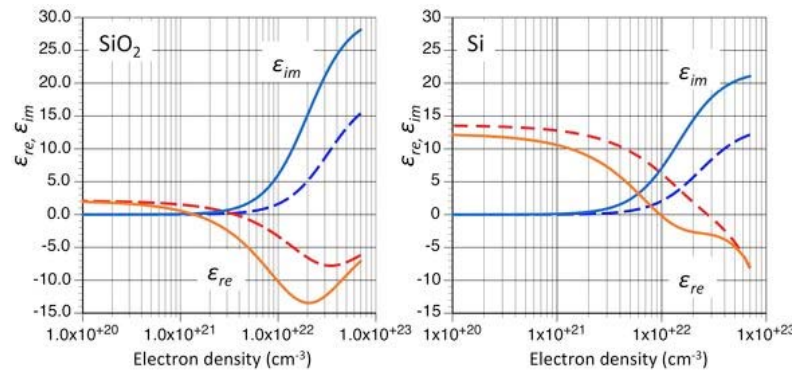


# Empirical ionization model based on rate equations for $n_e$ and $T_e$ & Drude model (Gamaly-Rode):

- Study the regime between ionization and ablation thresholds (ions are not moving)
- Scattering rate depends on electron temperature:  
grows with  $T_e$  at low  $T_e$ , then  $\sim T_e^{-3/2}$  near ablation threshold
- This dependence causes non-trivial dependence of Drude reflectivity on pulse fluence or on time along the pulse

$$\epsilon_{Re} = \epsilon_0 - (\epsilon_0 - 1) \frac{n_e}{n_{at}} - \frac{n_e}{n_{cr} \left[ 1 + \left( v_{eff}(T_e) / \omega \right)^2 \right]}$$

$$\epsilon_{Im} = \frac{n_e}{n_{cr} \left[ 1 + \left( v_{eff}(T_e) / \omega \right)^2 \right]} \cdot \frac{v_{eff}(T_e)}{\omega}$$

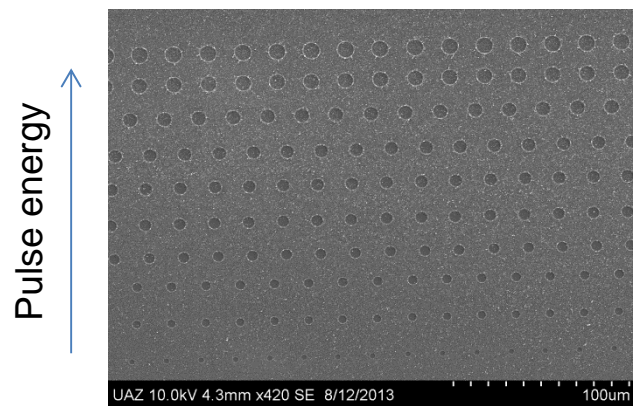


E. Gamaly, A. Rode, "Transient optical properties of dielectric excited by ultra-short laser pulse" (Submitted)



# Supporting experiments (UA)

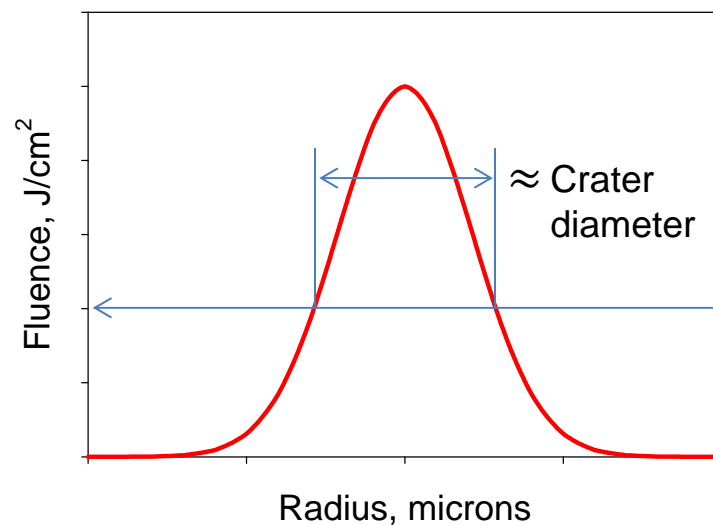
Studies of ionization dynamics – regime between ionization and ablation thresholds  
Measurements of transient dielectric function ( $\text{SiO}_2$ )



$$F(r) = \int_{-\infty}^{+\infty} e^{-2(r/R_{beam})^2} \cdot I(r=0, t) \cdot dt$$

$$F_{th} \approx e^{-2(r_{crat}/R_{beam})^2} \cdot \int_{-\infty}^{+\infty} I(r=0, t) dt$$

$$\frac{F(r=0)}{F_{th}} = e^{2(r_{crat}/R_{beam})^2}$$



Plot  $r_{crat}^2$  vs.  $\log(F) \Rightarrow F_{th}, R_{beam}$

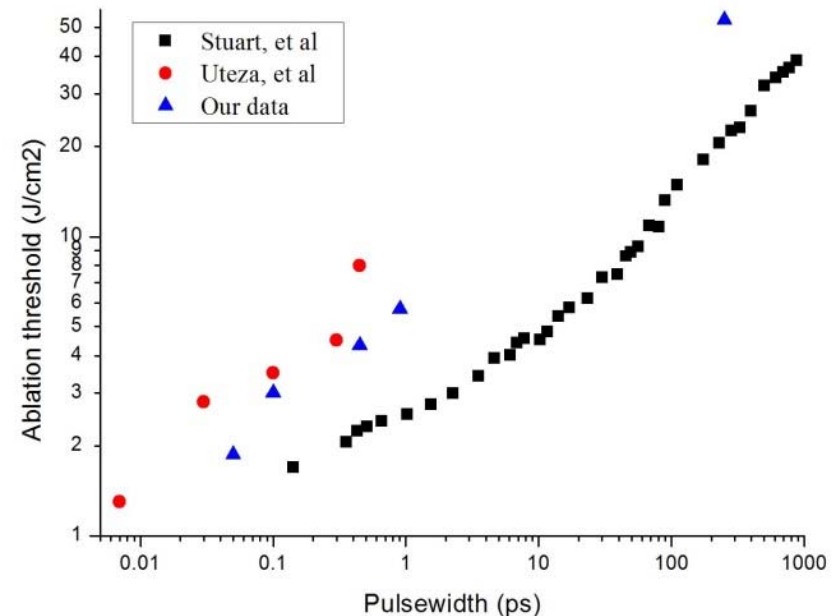
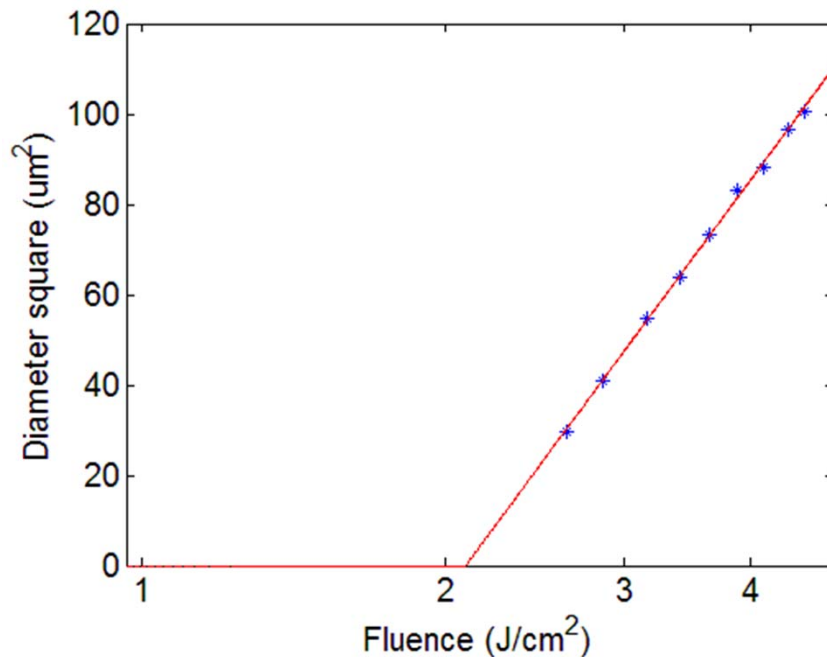
J. M. Liu, Opt. Lett. **7**, 196 (1982)

Ablation threshold fluence



# Supporting experiments (UA)

Studies of ionization dynamics – regime between ionization and ablation thresholds  
Measurements of transient dielectric function ( $\text{SiO}_2$ )



B. Stuart et al. (LLNL), JOSAB **13**, 459 (1996)

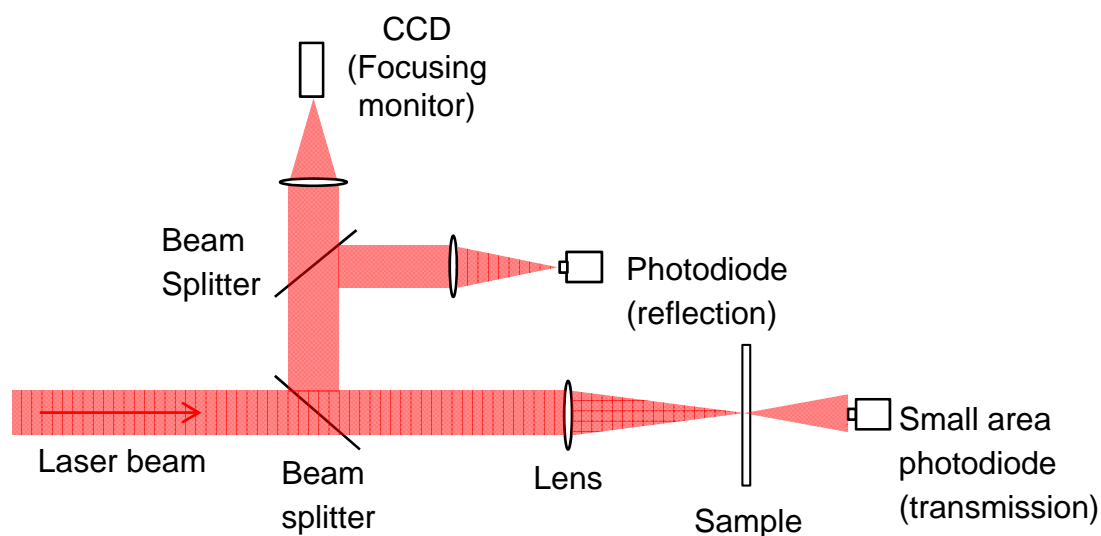
O. Uteza et al. (U. Marseille, INRS Quebec), Appl. Phys. A **105**, 131 (2011)

- Ablation threshold fluence  $2.1 \text{ J}/\text{cm}^2$  for 70 fs pulse
- Beam radius  $8.1 \text{ } \mu\text{m}$ , consistent with knife-edge measurement

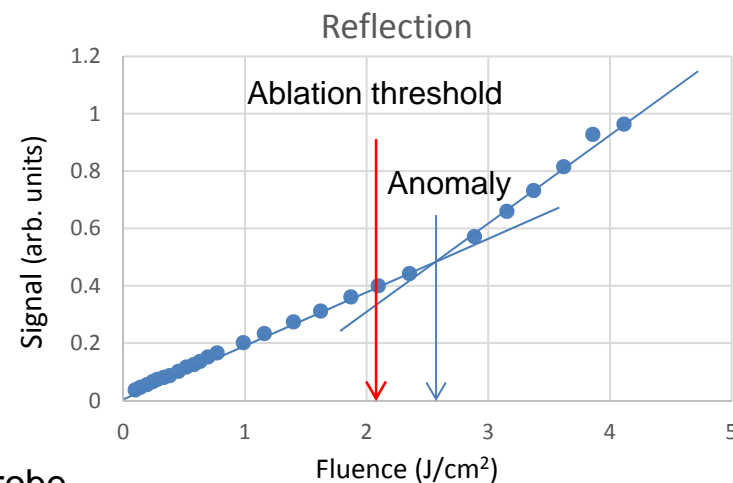
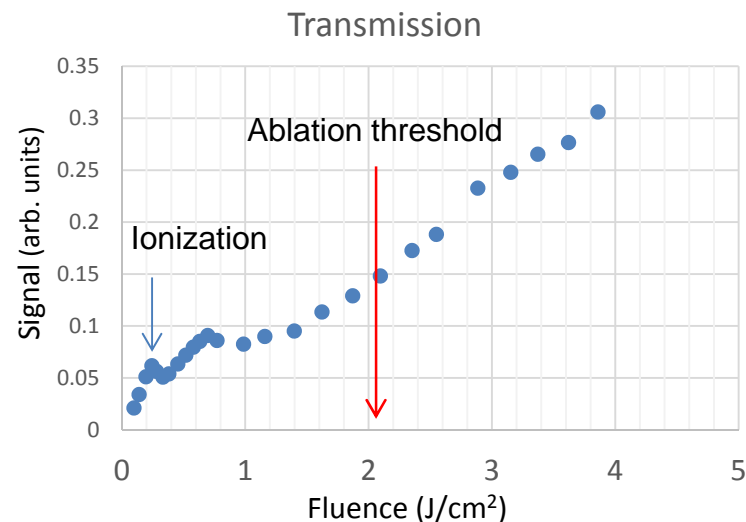


# Supporting experiments (UA)

## Measurements of ionization threshold – detect anomalies in transmission vs. energy



- Measure transmission anomalies in the range 0.2 – 1.0 J/cm<sup>2</sup>
- Data is difficult to interpret
- Will conduct pump-probe measurements of reflectivity with 5 fs probe





## Supporting experiments (UA)

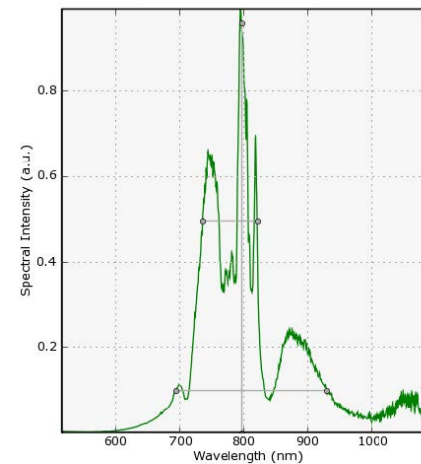
Hollow-fiber pulse compressor installed, being integrated into pump-probe setup.

Will allow transient reflectivity measurements with 5 fs resolution  
and ablation measurements in the ultrahigh intensity regime

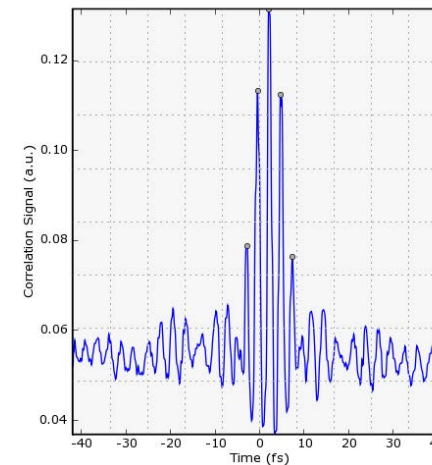


- Neon-filled 100  $\mu\text{m}$  diam. capillary, 1.5 bar.
- Max. compressed output: 0.68 mJ
- Min. pulse duration: 3.7 fringes = 5.1 fs

Spectrum



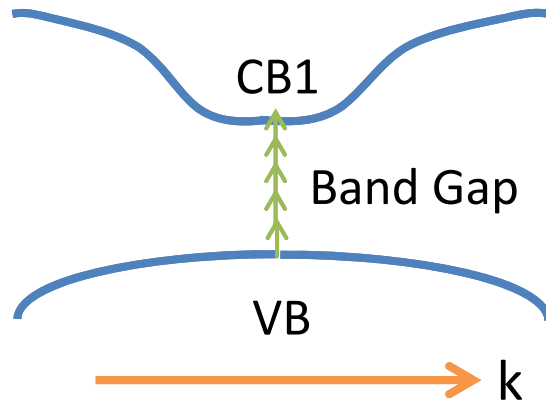
Autocorrelation





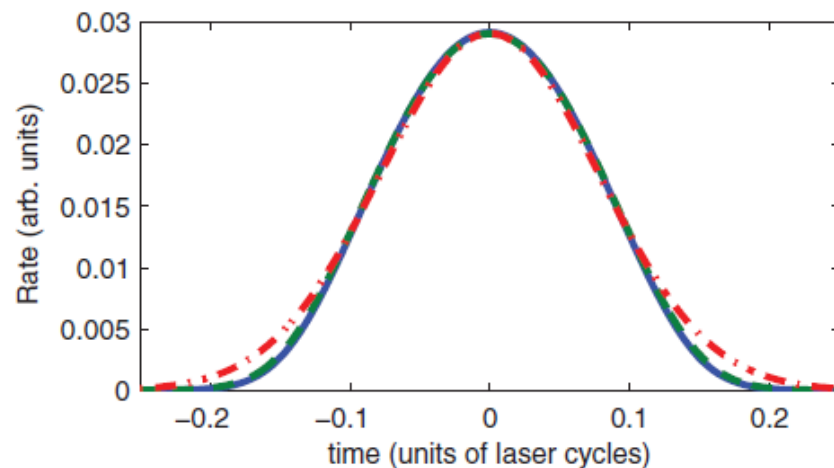


**For ultrashort pulses (<10 fs) and ultrahigh intensities (>10<sup>14</sup> W/cm<sup>2</sup>), sub-cycle effects in ionization become important (M. Ivanov – MBI)**



$$\frac{dn_e}{dt} = \underset{\substack{\text{MPI} \\ \downarrow}}{\sigma \cdot I^k} + \underset{\substack{\text{Avalanche} \\ \downarrow}}{\alpha \cdot I(t) \cdot n_e(t)}$$

Need non-perturbative treatment



Sub-cycle ionization rate:

- Blue – numerical integration
- Green – approx. analytical formula
- Red – Gaussian fit

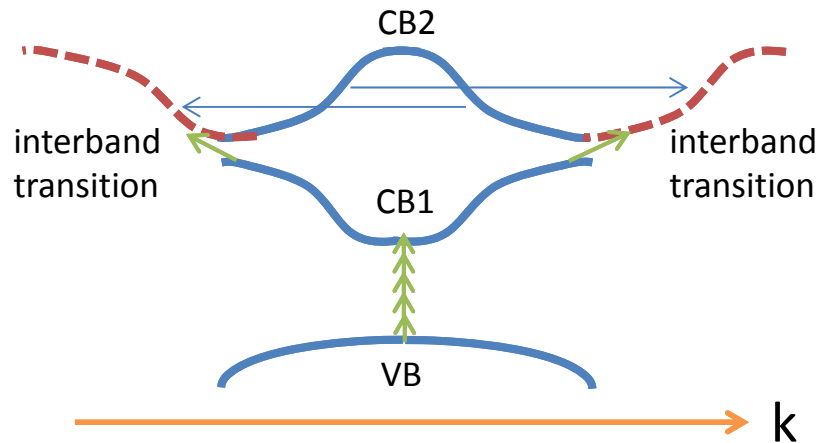
Work in progress:

Calibrate analytical formula against absolute cycle-averaged values measured for SiO<sub>2</sub>, for incorporation into the Maxwell code





**Related question: In dielectric crystals, what happens to the band structure in strong IR fields? What is the effective mass of conduction band electrons?**

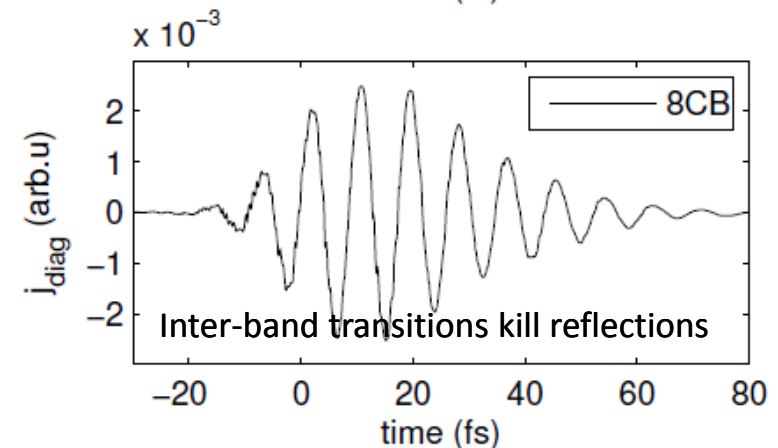
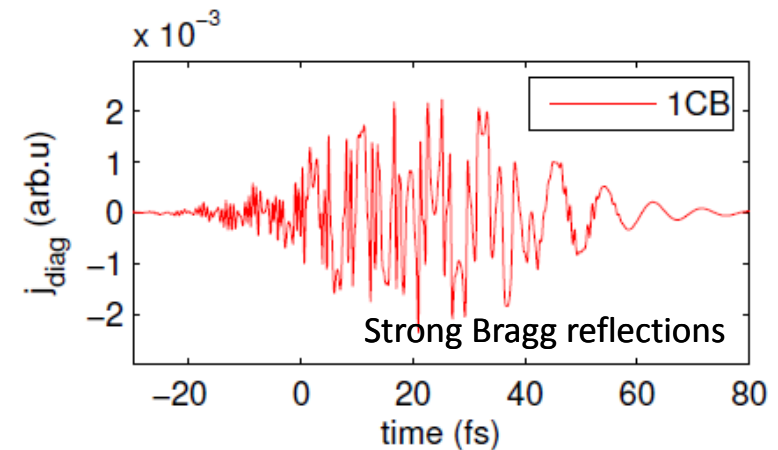


Pilot simulations:

- 1D periodic potential in an IR field
- Solve TDSE with 1 valence and different # of conduction bands

Results:

- Strong IR field eliminates band structure, creates a single effective parabolic band
- Conduction band electrons behave like free electrons with effective mass  $m=m_0$
- Harmonic generation strongly suppressed

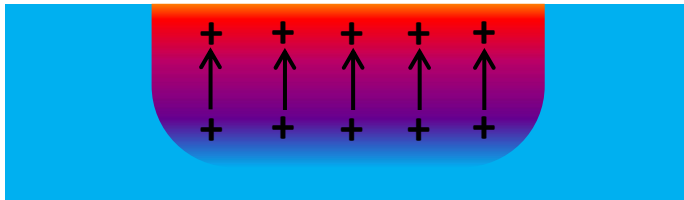




# First-principle models of fs laser-matter interactions

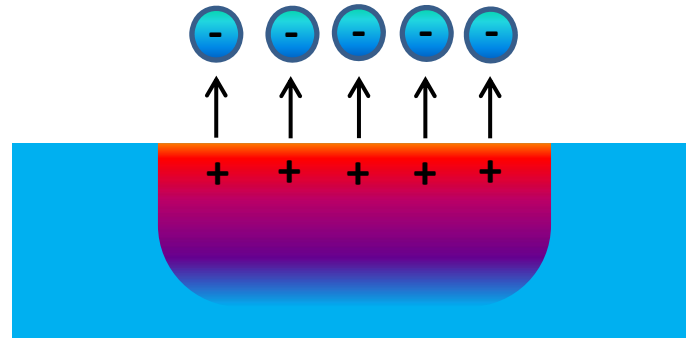
## Model #2 – First-principle model of surface ablation

Quantify relative contributions of Coulomb explosion and electrostatic ablation mechanisms



Coulomb explosion: Electrons leave, excessive positive charge pushes ions out of the material.

Some delay between departures of electrons and ions



Electrostatic ablation: Electron sheet pulls ions out of the material.

Electrons and ions leave simultaneously

E. Gamaly, A. Rode, V. Tikhonchuk, B. Luther-Davis, "Electrostatic mechanism of ablation by femtosecond lasers", Appl. Surface Science **197-198**, 699 (2002).

W. Roeterdink, L. Juurlink, O. Vaughan, J. Dura Diez, M. Bonn, A. Kleyn, "Coulomb explosion in femtosecond laser ablation of Si(111)", Appl. Phys. Lett. **82**, 4190 (2003).



## Model #2: Kohn & Sham model –

Quantum mechanics for electrons, classical mechanics for ions.

Computationally very challenging

– Can only treat 1D case with ~30 ions on a “conventional”  
(but still large) computer

- Electrons interact not individually but through the overall electron density  $n(r)$
- Driving of electrons by external field is described by vector potential  $A(r)$
- Coulomb interaction is described by total potential  $V(r, t, n)$ , which is the sum of electron and ion potentials
- Motion of individual ions is treated classically

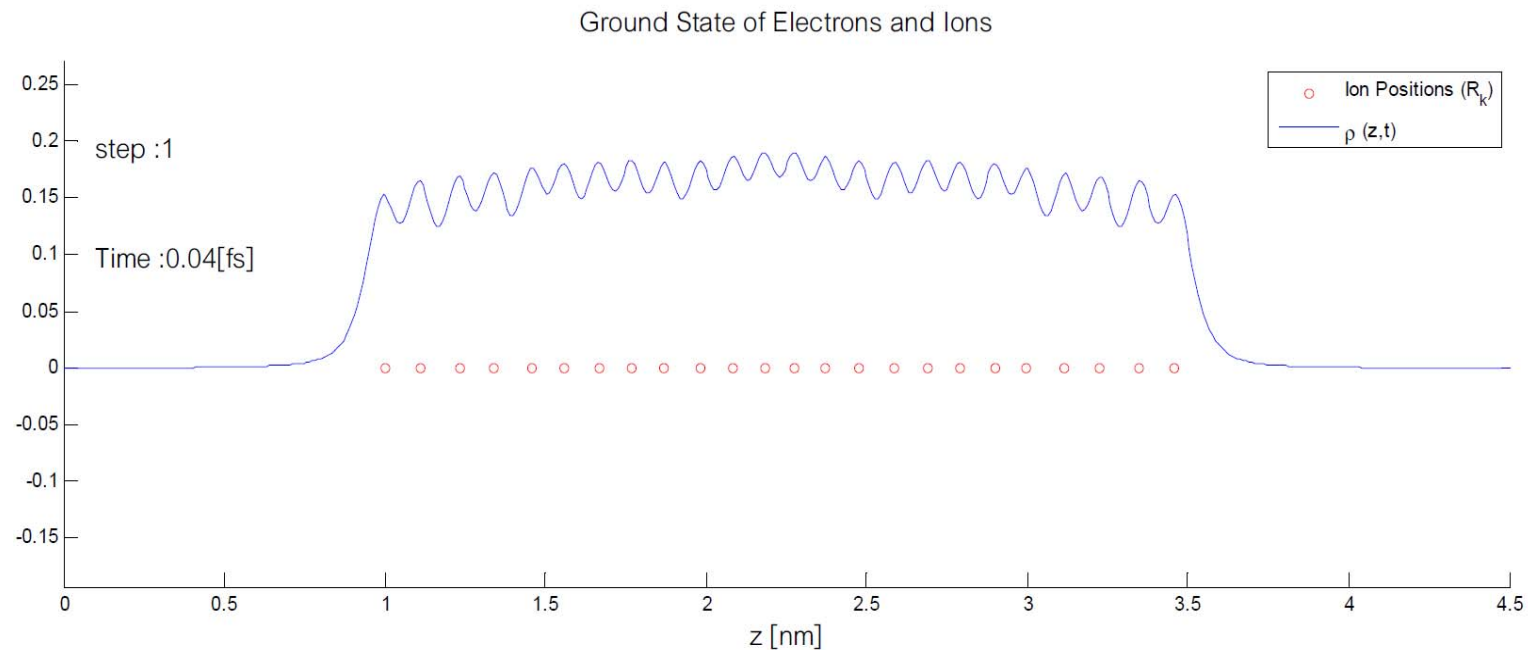
$$i\hbar \frac{\partial}{\partial t} \Psi_j = \frac{1}{2m_e} \left( \frac{\hbar}{i} \vec{\nabla} + e\vec{A} \right)^2 \Psi_j + V(\vec{r}, t, n) \Psi_j$$

$$V(\vec{r}, t, \rho) = e^2 \int \frac{n(\vec{r}', t)}{|\vec{r} - \vec{r}'|} d^3\vec{r}' + V_{xc}(n) - e^2 \sum_{n=1}^{N_Z} \frac{Z_n}{|\vec{r} - \vec{R}_n|}$$

$$m_n \frac{\partial^2 \vec{R}_n}{\partial t^2} = Z_n Z_m e^2 \sum_{m \neq n}^{N_Z} \frac{\vec{R}_n - \vec{R}_m}{|\vec{R}_n - \vec{R}_m|^3} + e^2 Z_n \vec{\nabla}_{\vec{R}_n} \int \frac{n(\vec{r}, t)}{|\vec{r} - \vec{R}_n|} d^3\vec{r}$$



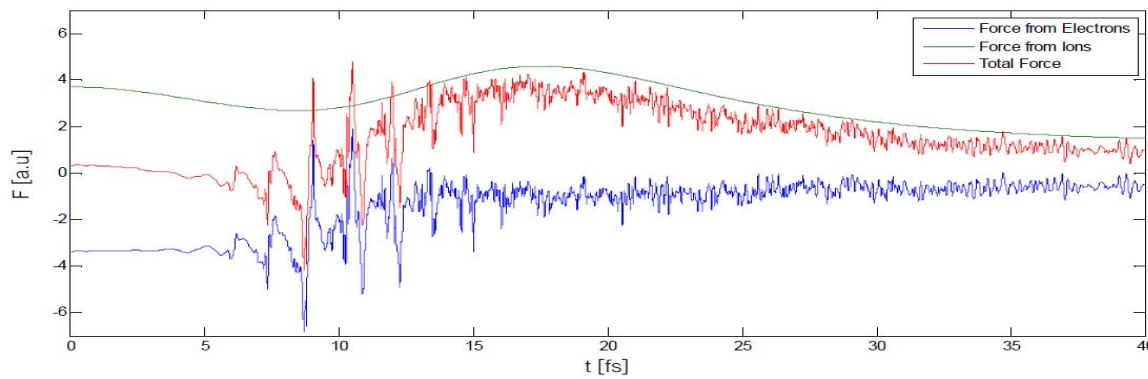
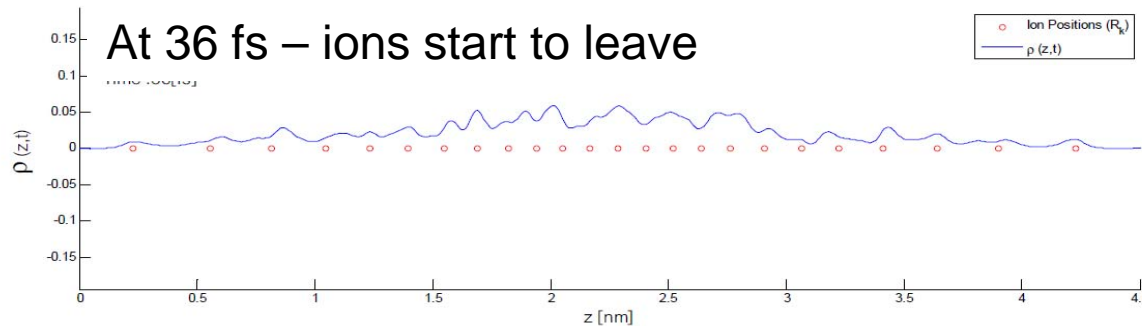
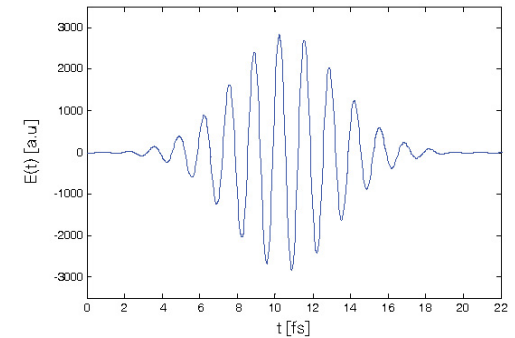
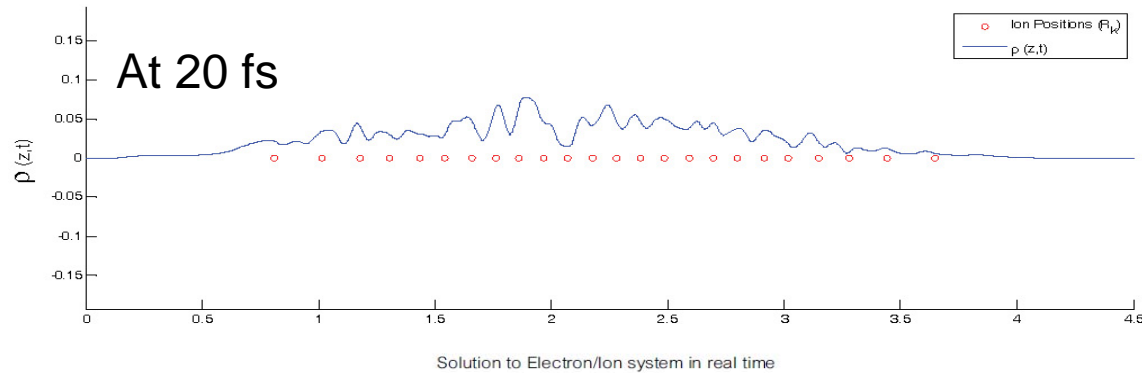
# Compute 1D ground state (prior to arrival of laser pulse)



- Computed initial ground state (shown)
- 24 ions (red) are computed, typical distances of  $\sim 1.1$  Angstroms
- Total electron probability density (blue) computed as sum of 48 electron probability densities



# 1D string of ions + electrons excited by 20fs laser pulse

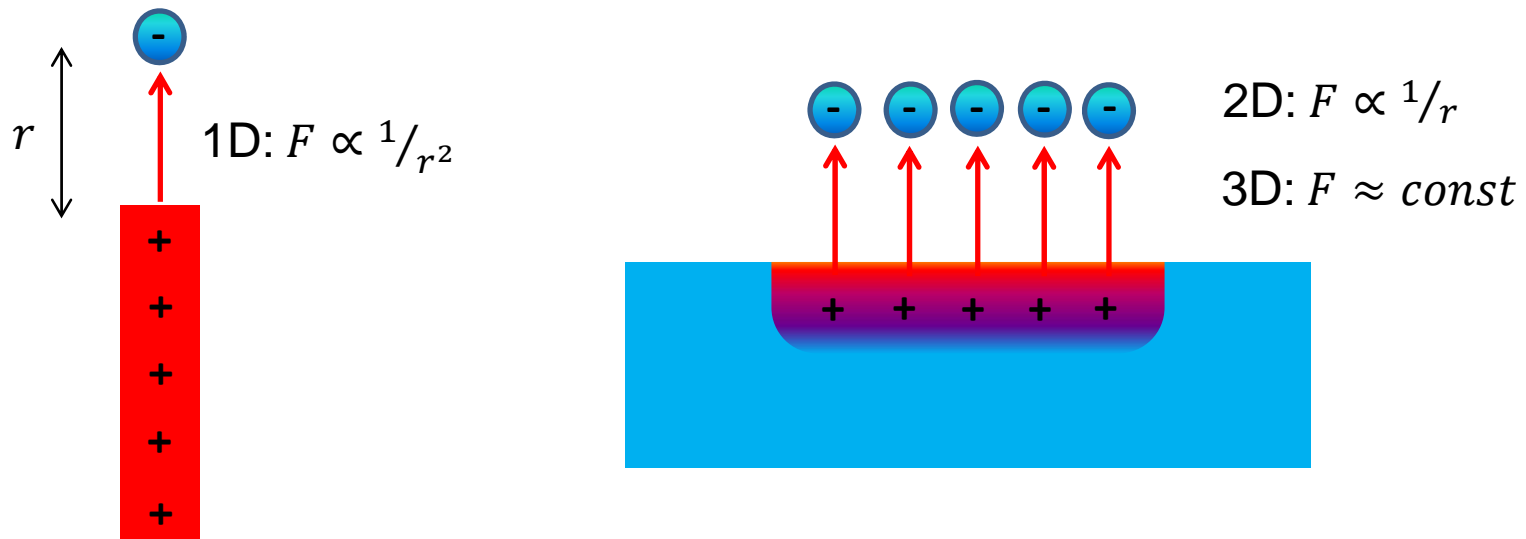


Forces acting on the edge ion – pushing by other ions dominates over pulling by electrons

Coulomb explosion wins in 1D



# 1D, 2D and 3D cases are qualitatively different



DFT treatment of realistic sample sizes, even in 2D, is impractical:  
(800 nm)<sup>2</sup> 2D sample contains  $\sim 10^7$  ions  $\rightarrow 5^{18}$  bytes simulation - huge

On-going work:

- Implement a semi-classical model instead
  - Electrons and ions are treated as classical particles, with the addition of a velocity-dependent potential preventing electrons falling on ions

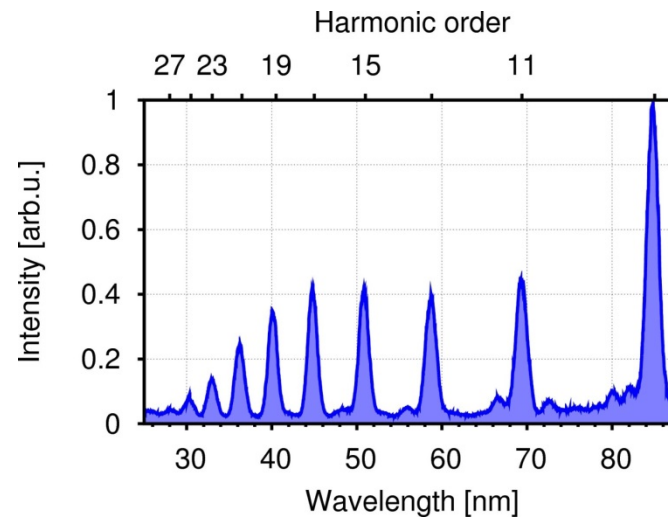
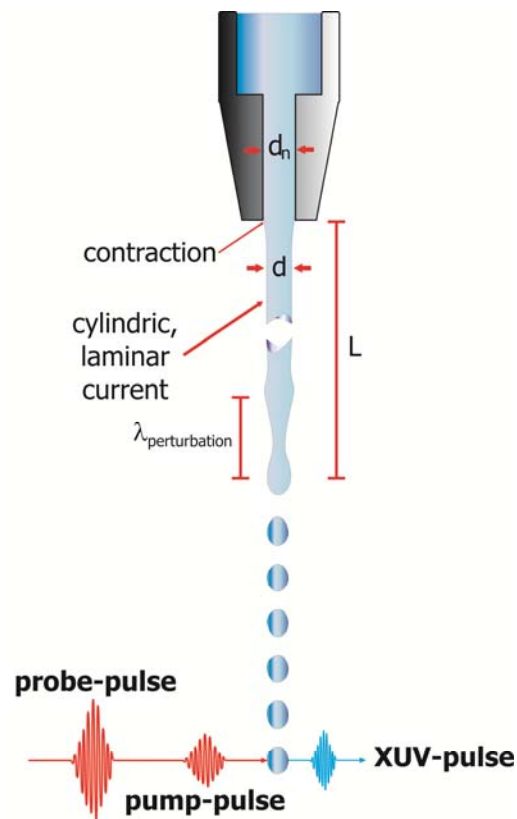
(Erik Lotstedt, T. Kato, K. Yamanouchi, “Classical dynamics of laser-driven D3+” (PRL **106**, 203001 (2011))



# Supporting experiments

(Hannover – Uwe Morgner, Milutin Kovacev, Heiko Kurz)

So far studied high harmonic generation in water microdroplets driven by pairs of fs pulses separated by several nanoseconds



- Pump intensity:  $3.7 \times 10^{14} \text{ W/cm}^2 \rightarrow \sim 40 \text{ J/cm}^2$
- Pump-probe delay: 1 ns
- Harmonics of up to the 27<sup>th</sup> order generated

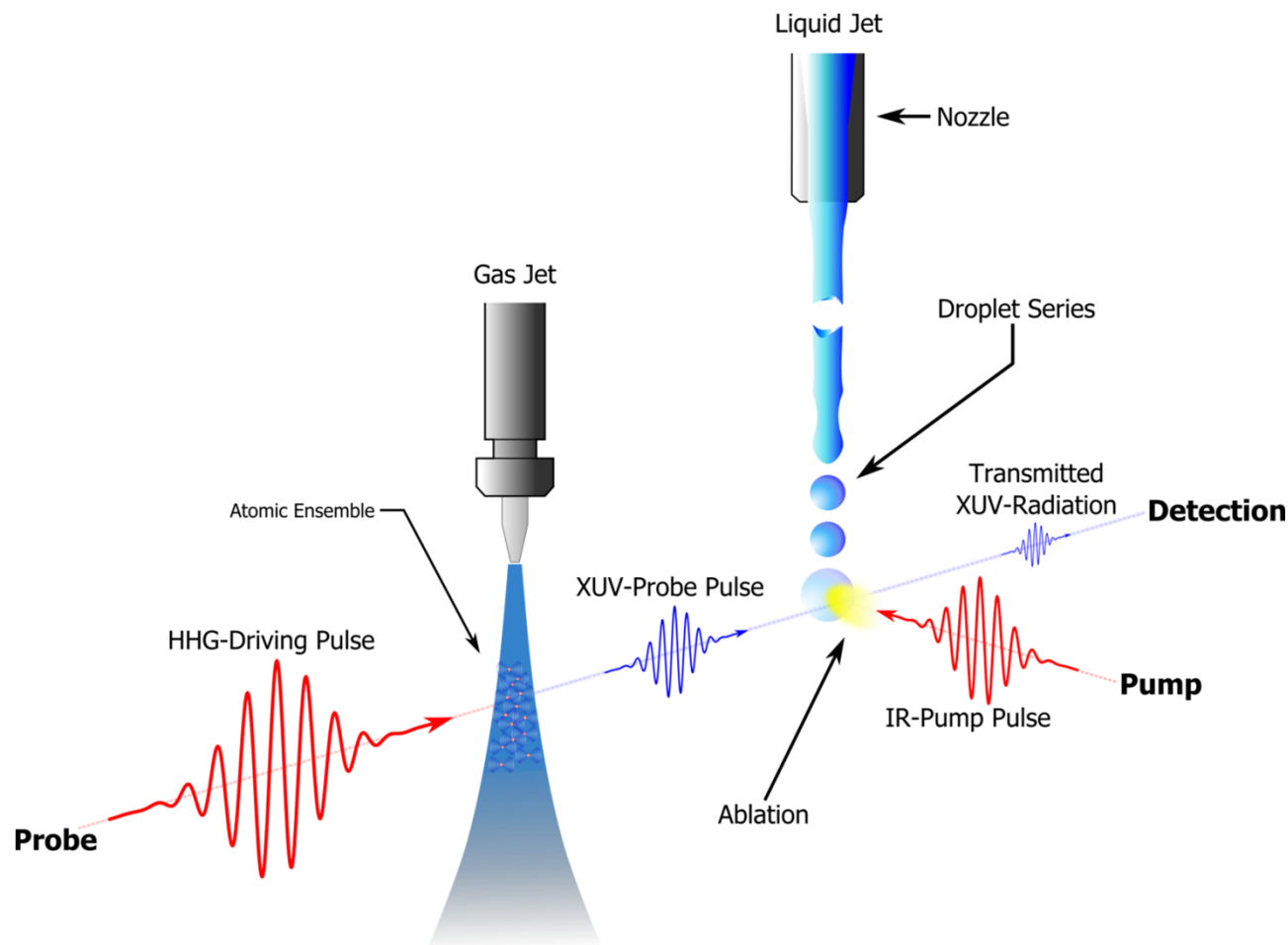
H. Kurz, D. Steingrube, D. Ristau, M. Lein, U. Morgner, M. Kovacev,  
“High-order-harmonic generation from dense water microdroplets”, PRA **87**, 063811 (2013)



# Supporting experiments

(Hannover – Uwe Morgner, Milutin Kovacev, Heiko Kurz)

Imaging of laser ablation of microdroplets in orthogonal pump-probe setup incorporating optical and XUV probe beams





# Exotic situations of fs laser-matter interactions

Update on confined microexplosion experiments at ANU:

Creation of new phases of Si through microexplosion on Si-SiO<sub>2</sub> interface

(A. Rode, E. Gamaly, with Chris Pickard from Univ. College London)

## Method:

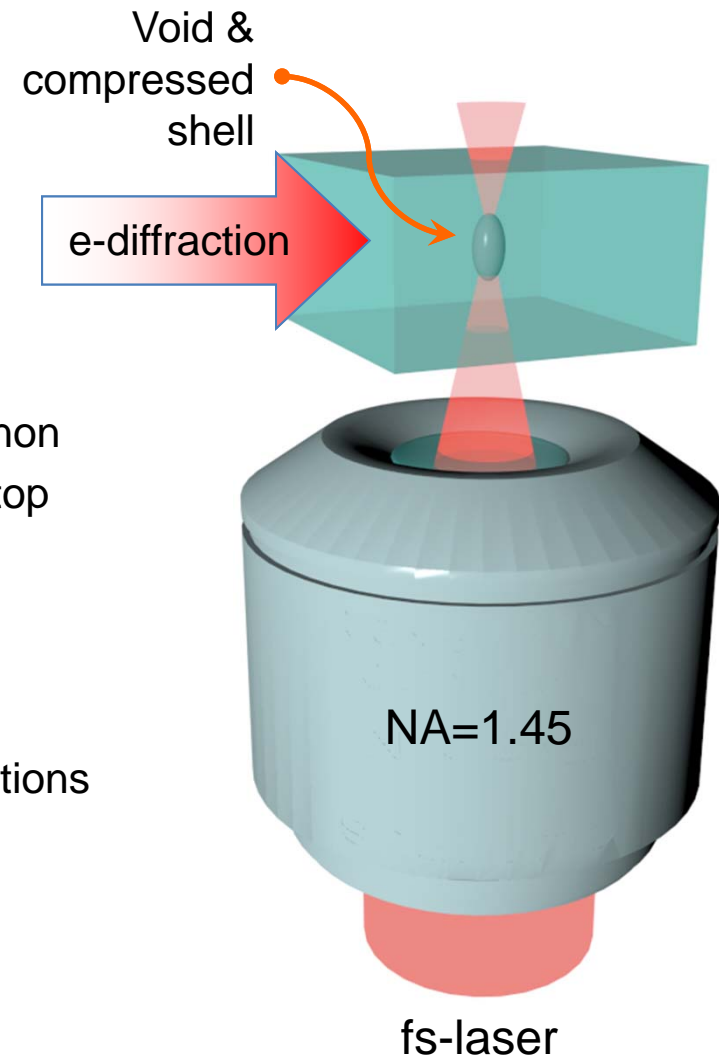
Confined micro-explosion by ultrafast-laser  
focused in the bulk of transparent material  
– conservation of mass

## Motivation:

Formation of material states at extreme pressure and non  
equilibrium temperature conditions in laboratory table-top  
experiments

## Outcome:

- New materials:  
high-pressure  $\leftrightarrow$  ultra-hard; insulator-metal transitions
- New material phases (metastable?);
- New chemical/physical  
properties of “shocked” materials





# History of microexplosion studies



## **I – Indication on the creation of high pressure >TPa (10 Mbar) with fs-laser:**

E. Glezer, E. Mazur, “Ultrafast-laser driven microexplosion in transparent materials”, Appl.Phys. Lett. **71**, 882–884 (1997)

## **II – Experimental evidence of the >3 TPa pressures in sapphire:**

S. Juodkazis, et al., “Laser-induced microexplosion confined in the bulk of a sapphire crystal: Evidence of multimegabar pressures”, PRL **96**, 166101 (2006)

## **III – Discovery of the creation of super-dense material phases inside microexplosion voids:**

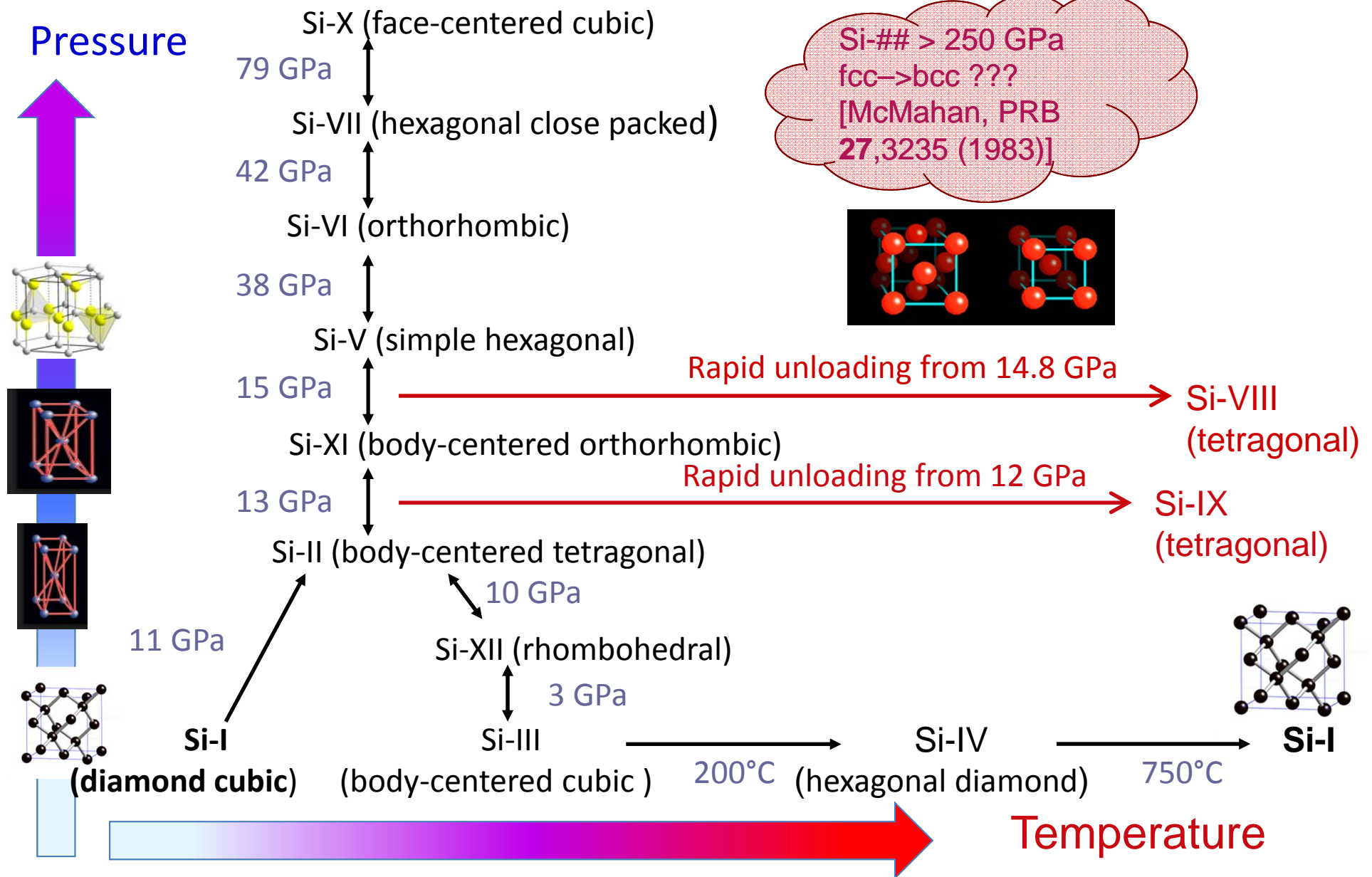
A. Vailionis, E. Gamaly, V. Mizeikis, W. Yang, A. Rode, S. Juodkazis, “Evidence of superdense aluminium synthesized by ultrafast microexplosion”, Nature Communications **2**, 445 (2011)

## **IV – Laser-driven microexplosion on a material interface, densification of opaque materials**

L. Rapp, B. Haberl, J. Bradby, E. Gamaly, J. Williams, A. Rode, “Confined microexplosion induced by ultrashort laser pulse at SiO<sub>2</sub>/Si interface”, Appl. Phys. A **114**, 33 (2014)



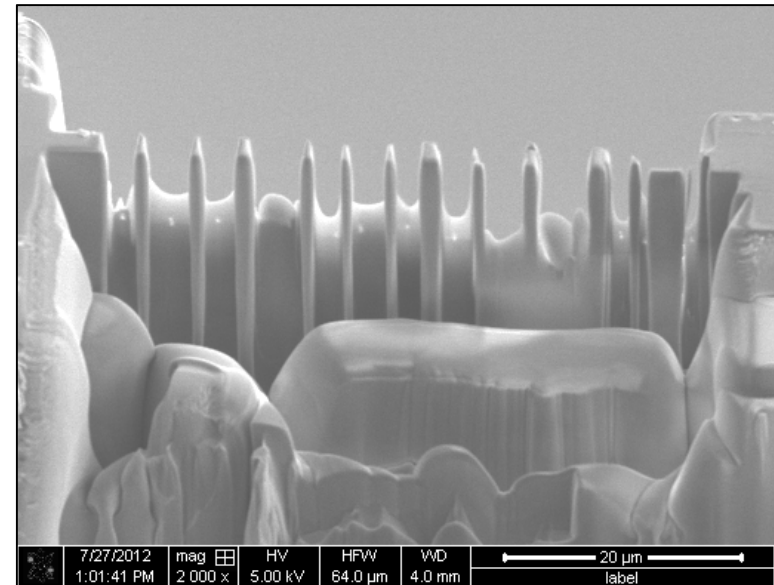
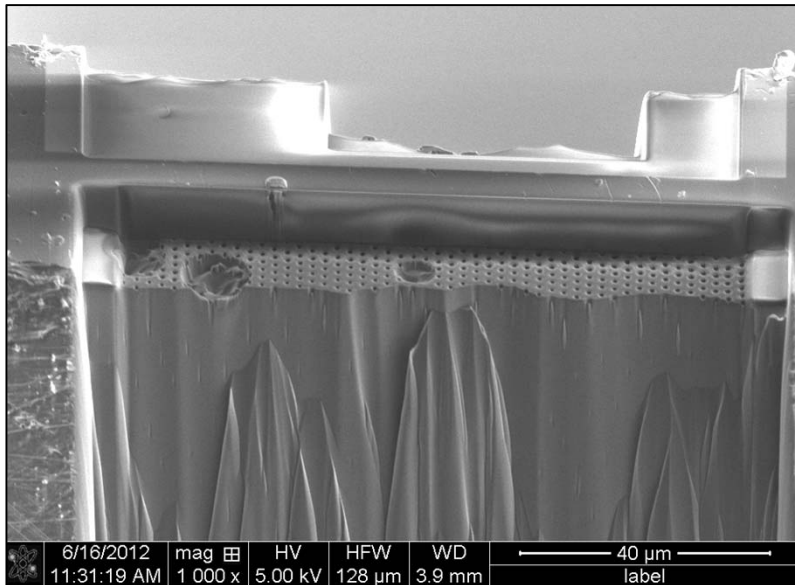
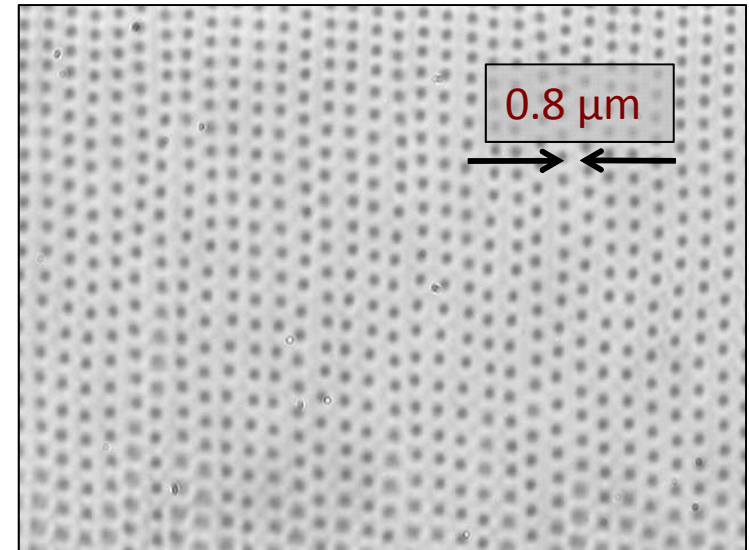
# Phase transitions of dc-Si to metallic Si





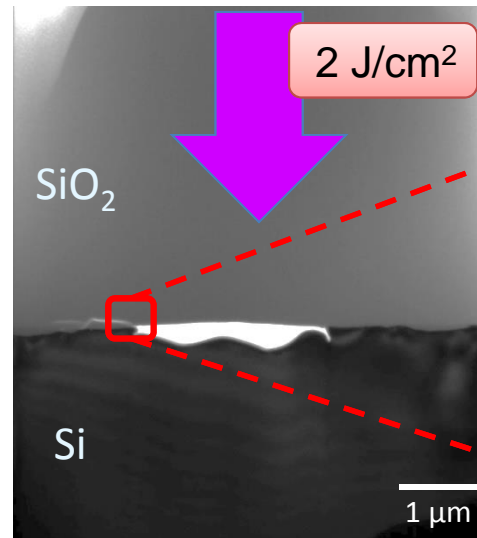
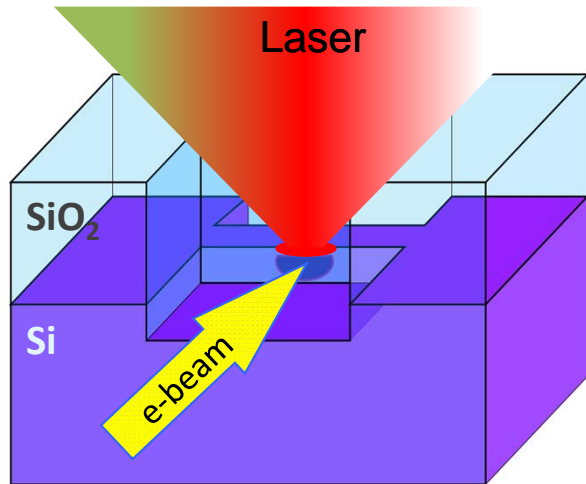
# Preparation of samples for TEM and e-diffraction

- Preparation of arrays of micro-explosions  
~10  $\mu\text{m}$  under the surface, ~1  $\mu\text{m}$  apart;
- Polishing and cutting to 100- $\mu\text{m}$  thick sample
- Removal of 10- $\mu\text{m}$  thin surface layer with  
a focused ion beam (FIB)
- Thinning lamella to <100 nm for TEM

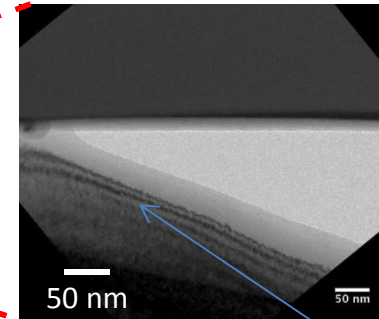




# TEM imaging of voids on material interfaces

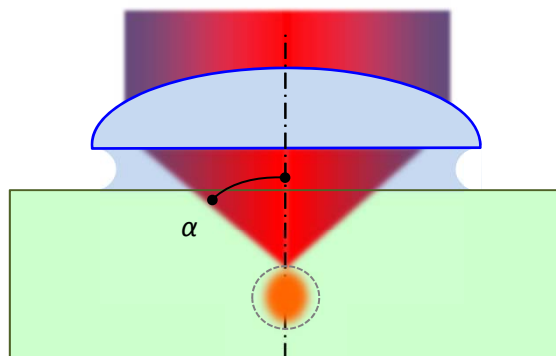


Below threshold  
 $>2 \text{ J/cm}^2$  in  $\text{SiO}_2$   
 ( $\text{SiO}_2$  remains intact)

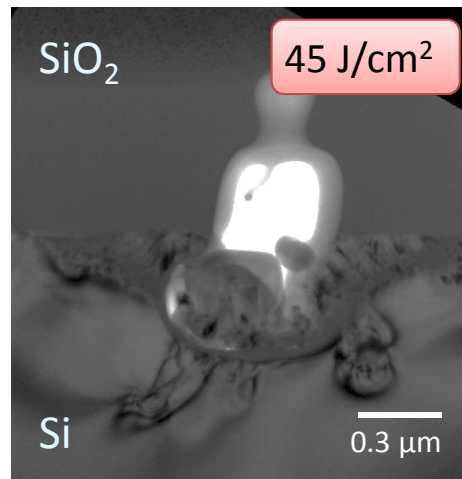


Amorphous Si

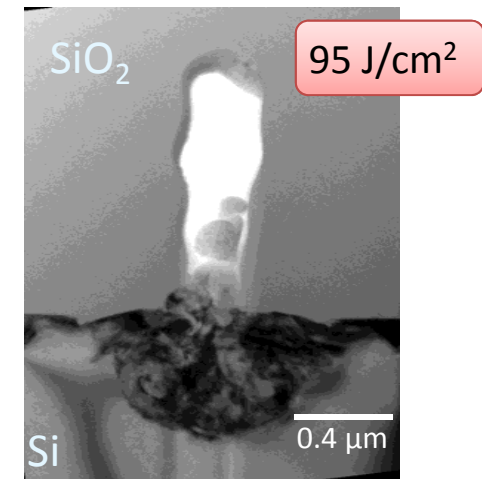
High N.A. with x150



$$r_f = 0.368 \text{ µm}$$



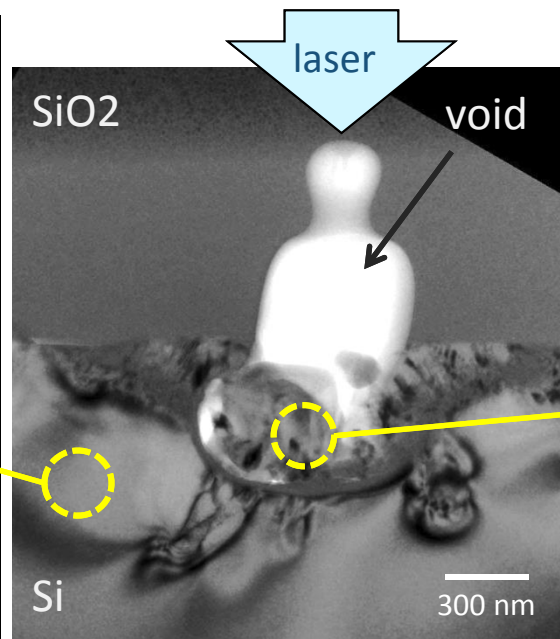
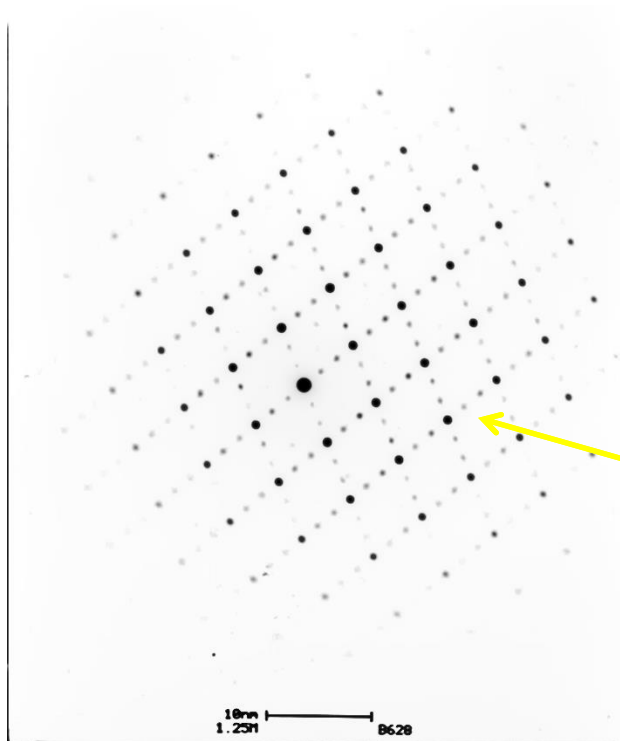
Above threshold in  $\text{SiO}_2$   
 (Absorption in  $\text{SiO}_2$ )



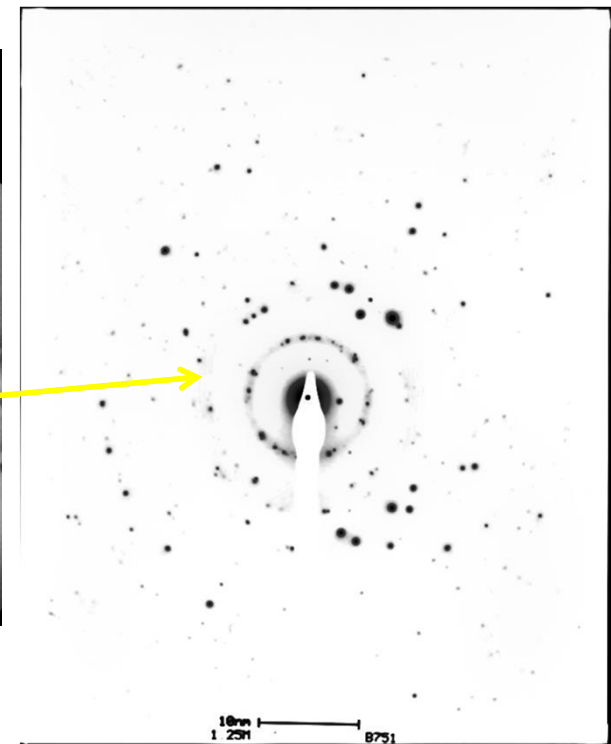


# Electron diffraction reveals new material phases

Conventional  
diamond-cubic Si



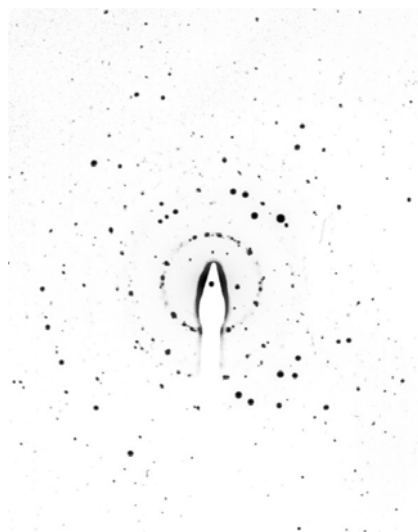
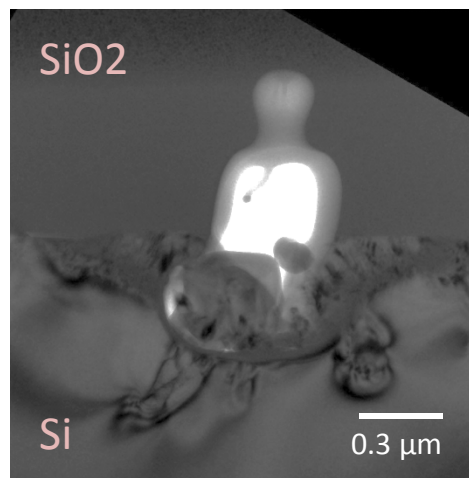
Si  
quenched from WDM state



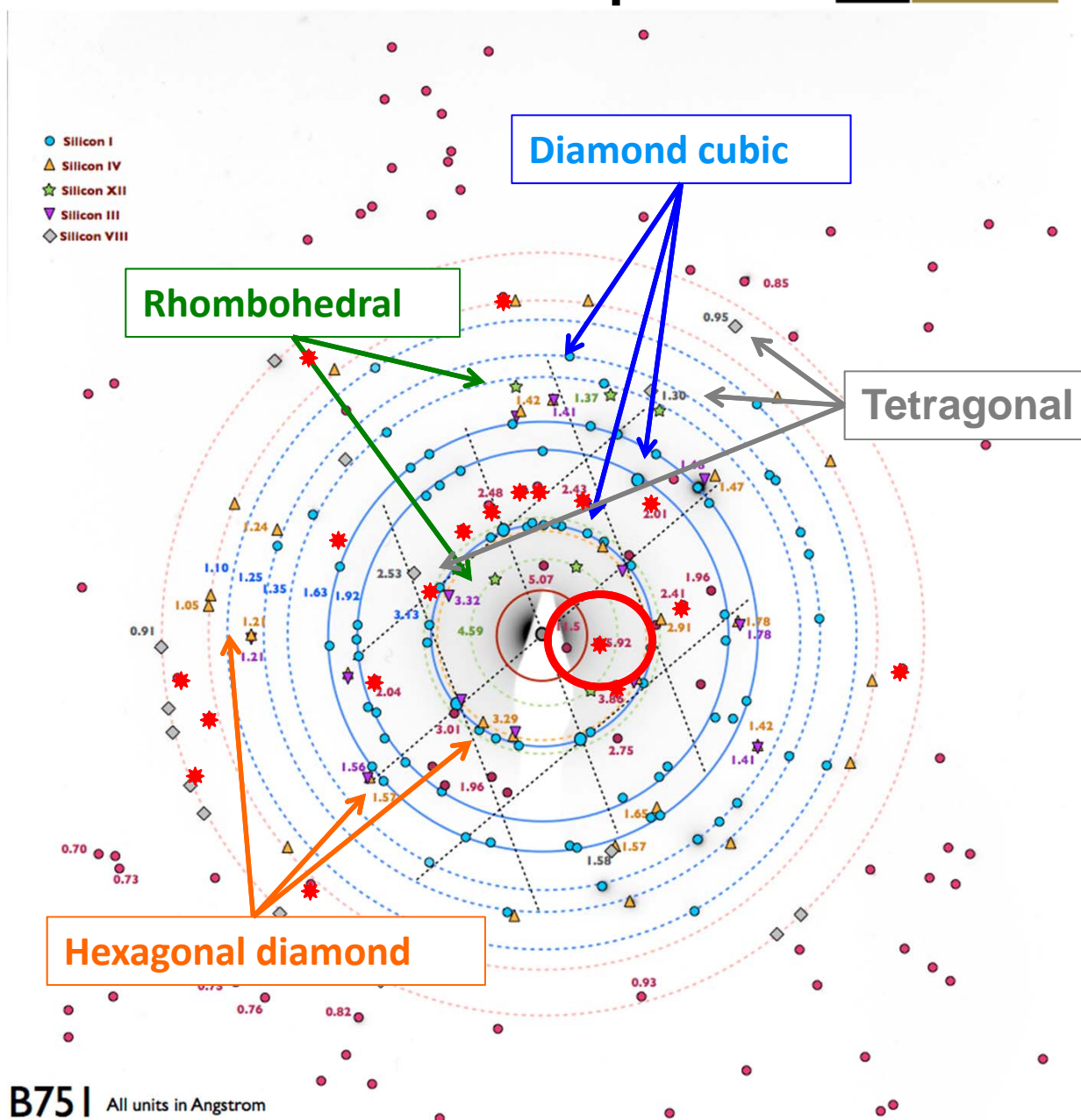


# Electron diffraction reveals new material phases

45 J/cm<sup>2</sup>

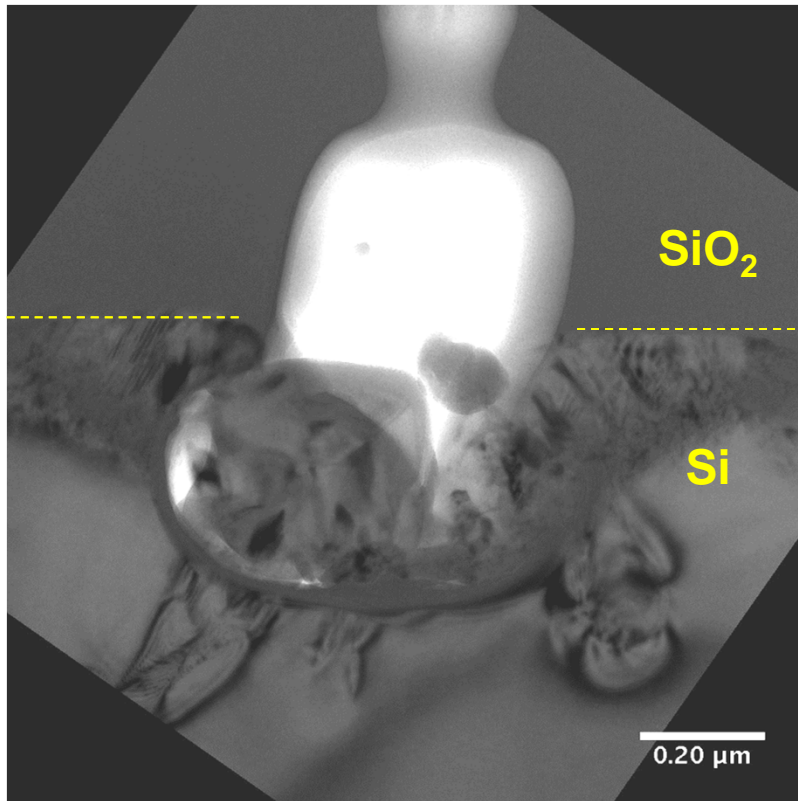


Electron diffraction at 300 kV  
data #B751

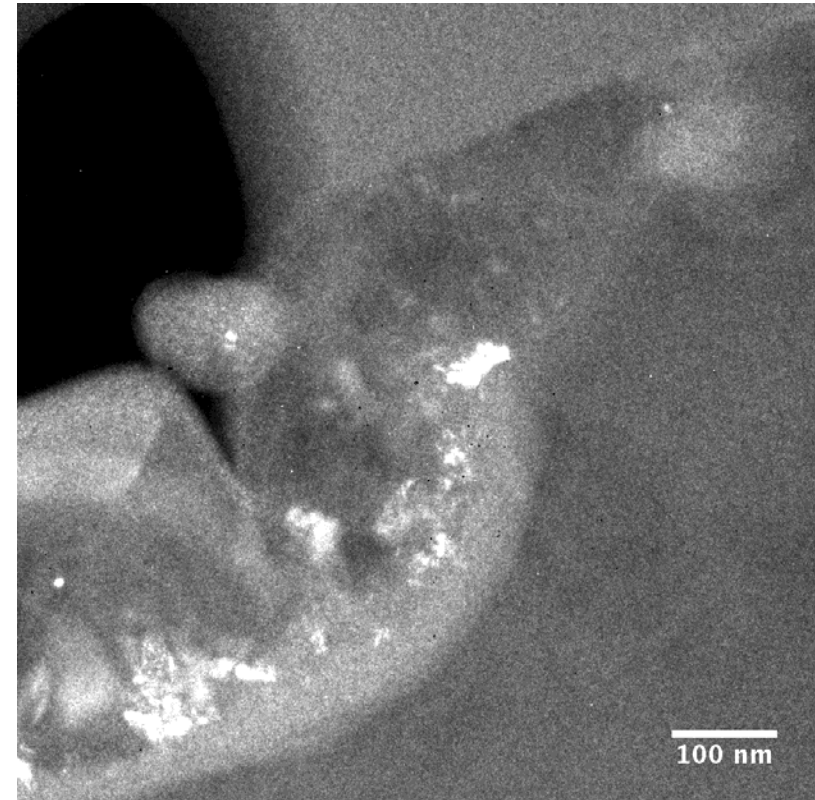




# TEM within a particular diffraction order shows spatial locations of new material phases



TEM image of void at Si/SiO<sub>2</sub> interface



Bright-field image at 5.92 Å bright spot



## Results so far:

- First observation of two new tetragonal phases of silicon: 16-atom Si-BT8 (probably metallic) and 12-atom Si-ST12 (probably narrow-band SC)
- Demonstration of low kinetic barrier in non-equilibrium conditions for formation of new metastable phases – synthesis of phases directly from WDM
- BT8-Si density is  $2.73 \text{ g/cm}^3$  at 5 GPa, which is about 17% more dense than dc-Si. Computed density of states indicate the phase is a narrow band gap semiconductor
- ST12-Si density is  $2.47 \text{ g/cm}^3$ , 6% more dense than dc-Si at ambient pressure. Density of states indicate the phase is an indirect bandgap semiconductor with a bandgap energy between 1.1 eV and 1.67 eV
- These metastable phases are of significant interest, as they may have new electronic and photovoltaic properties



# Summary

1. **First-principle modeling of fs laser-matter interactions**
  - Inside dielectrics: Non-paraxial Maxwell propagator coupled with ionization
  - On surfaces: DFT model of ablation – computationally very challenging, implement a simpler semi-classical model
  - Sub-cycle effects in ionization with ultrashort pulses ( $<10$  fs)
  - Modifications of band structure of crystals in ultraintense laser fields
2. **Supporting experiments:**
  - Investigations of regimes between ionization and ablation thresholds
  - Measurements of transient reflectivity of ionized dielectrics using 5 fs probe pulse
  - Imaging of ions created through fs ablation of microdroplets with XUV probe
3. **Experimental studies of exotic ablation situations:**
  - Confined microexplosion inside transparent solids and on interfaces
  - Creation and identification of new super-dense material phases
  - Ablation with ultrashort laser pulses  $\sim 5$  fs – sub-cycle ionization effects in ablation

